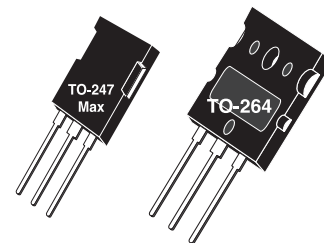


## Ultra Fast NPT - IGBT®

The Ultra Fast NPT - IGBT® is a new generation of high voltage power IGBTs. Using Non-Punch-Through Technology, the Ultra Fast NPT-IGBT® offers superior ruggedness and ultrafast switching speed.



### Features

- Low Saturation Voltage
- Low Tail Current
- RoHS Compliant 
- Short Circuit Withstand Rated
- High Frequency Switching
- Ultra Low Leakage Current

Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is recommended for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).



### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Ratings	Unit
$V_{ces}$	Collector Emitter Voltage	1200	V
$V_{GE}$	Gate-Emitter Voltage	$\pm 30$	
$I_{C1}$	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	170	A
$I_{C2}$	Continuous Collector Current @ $T_C = 100^\circ\text{C}$	85	
$I_{CM}$	Pulsed Collector Current <sup>①</sup>	340	
SCWT	Short Circuit Withstand Time: $V_{CE} = 600V, V_{GE} = 15V, T_C = 125^\circ\text{C}$	10	$\mu\text{s}$
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	962	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 1.0\text{mA}$ )	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 2.5\text{mA}, T_J = 25^\circ\text{C}$ )	3.5	5.0	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 85A, T_J = 25^\circ\text{C}$ )		2.5	3.2	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 85A, T_J = 125^\circ\text{C}$ )		3.3		
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 170A, T_J = 25^\circ\text{C}$ )		3.5		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 1200V, V_{GE} = 0V, T_J = 25^\circ\text{C}$ ) <sup>②</sup>		10	1000	$\mu\text{A}$
	Collector Cut-off Current ( $V_{CE} = 1200V, V_{GE} = 0V, T_J = 125^\circ\text{C}$ ) <sup>②</sup>		100		
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			$\pm 250$	nA

 **CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.**

DYNAMIC CHARACTERISTICS

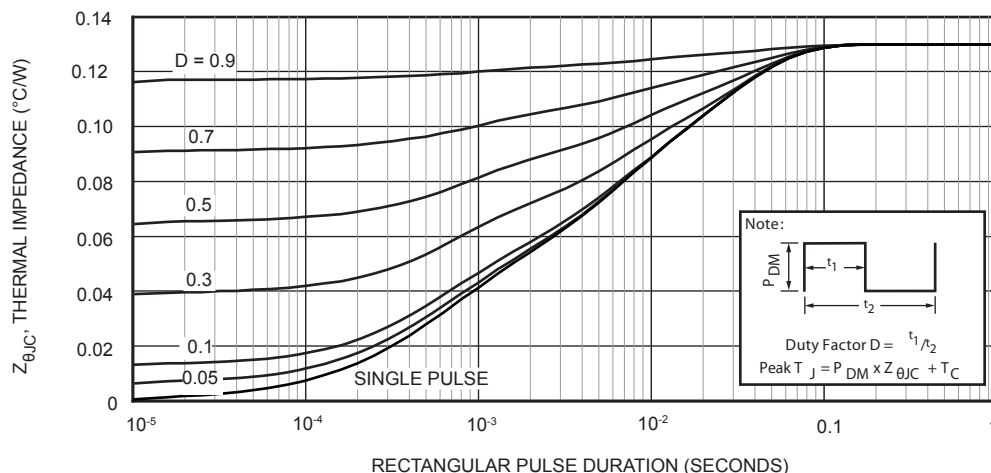
APT85GR120B2\_L

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1MHz$		8400		pF
$C_{oes}$	Output Capacitance			725		
$C_{res}$	Reverse Transfer Capacitance			190		
$V_{GEP}$	Gate to Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 85A$		7.5		V
$Q_g^{(3)}$	Total Gate Charge			490	660	
$Q_{ge}$	Gate-Emitter Charge			60	85	
$Q_{gc}$	Gate- Collector Charge			230	320	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 85A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +25^\circ C$		43		ns
$t_r$	Current Rise Time			70		
$t_{d(off)}$	Turn-Off Delay Time			300		
$t_f$	Current Fall Time			85		
$E_{on2}^{(5)}$	Turn-On Switching Energy			6000	9000	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			3800	5700	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 85A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +125^\circ C$		43		ns
$t_r$	Current Rise Time			70		
$t_{d(off)}$	Turn-Off Delay Time			350		
$t_f$	Current Fall Time			95		
$E_{on2}^{(5)}$	Turn-On Switching Energy			7800	11,700	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			4900	7350	

THERMAL AND MECHANICAL CHARACTERISTICS

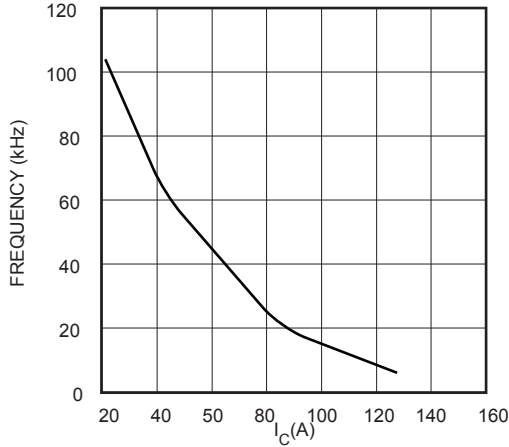
Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)			.13	°C/W
$R_{\theta JA}$	Junction to Ambient Thermal Resistance			40	
$W_T$	Package Weight	B2	.22		oz
		L	6		g
			.36		oz
			10		g

- 1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.
  - 2 Pulse test: Pulse Width < 380μs, duty cycle < 2%.
  - 3 See Mil-Std-750 Method 3471.
  - 4  $R_G$  is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)
  - 5  $E_{on2}$  is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.
  - 6  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.
- Microsemi reserves the right to change, without notice, the specifications and information contained herein.

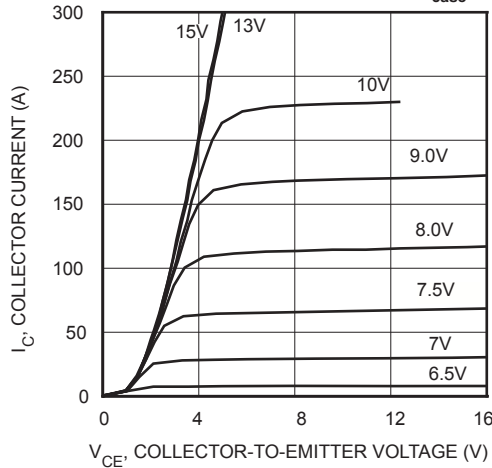


**TYPICAL PERFORMANCE CURVES**

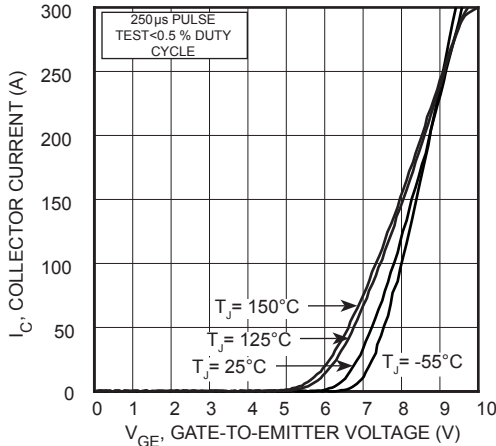
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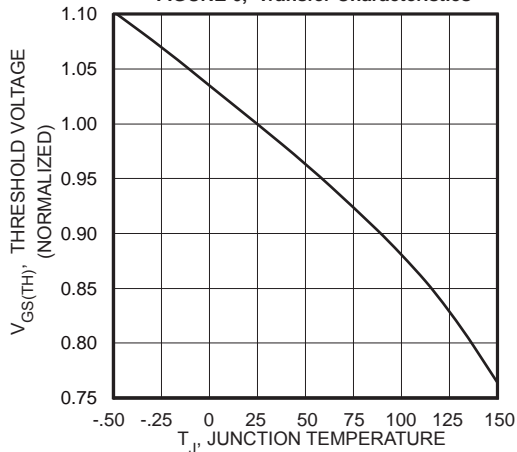
**FIGURE 2, Max Frequency vs Current ( $T_{case} = 75^{\circ}C$ )**



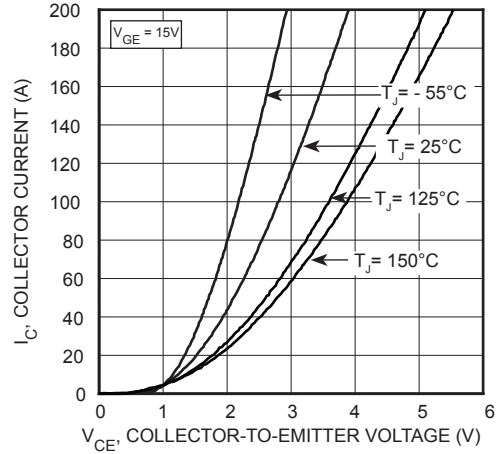
**FIGURE 4, Output Characteristics ( $T_J = 25^{\circ}C$ )**



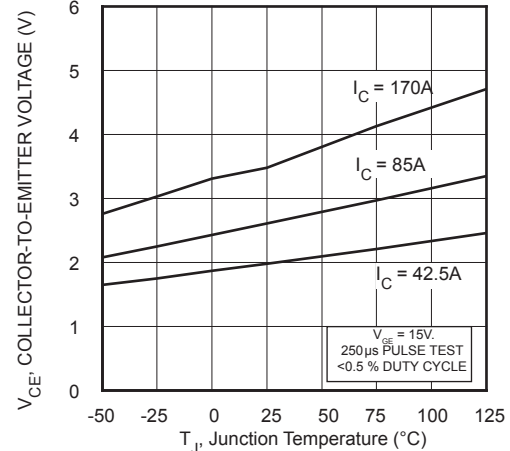
**FIGURE 6, Transfer Characteristics**



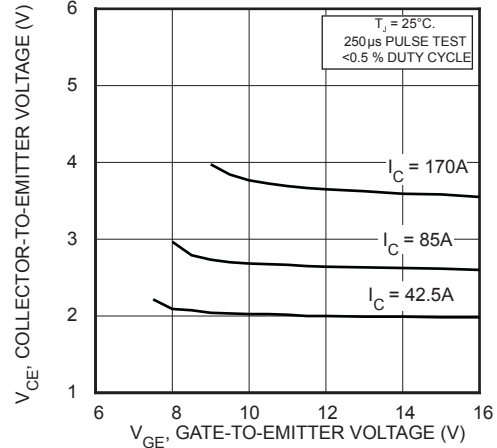
**FIGURE 8, Threshold Voltage vs Junction Temperature**



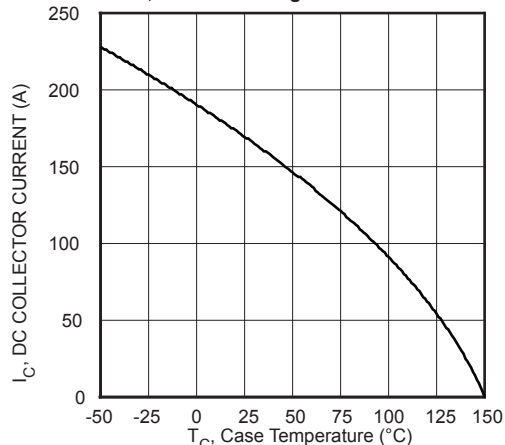
**FIGURE 3, Saturation Voltage Characteristics ( $T_J = 25^{\circ}C$ )**



**FIGURE 5, On State Voltage vs Junction Temperature**



**FIGURE 7, On State Voltage vs Gate-to-Emitter Voltage**



**FIGURE 9, DC Collector Current vs Case Temperature**

TYPICAL PERFORMANCE CURVES

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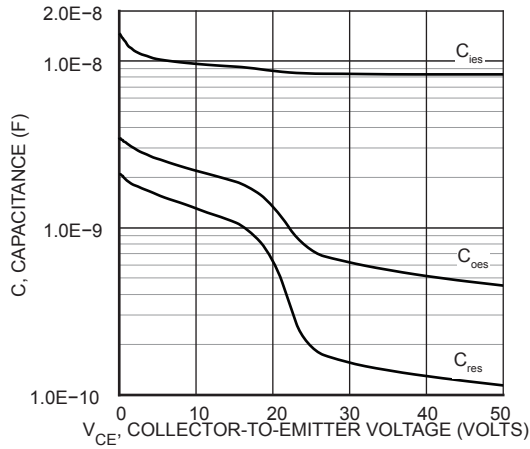


FIGURE 10, Capacitance vs Collector-To-Emitter Voltage

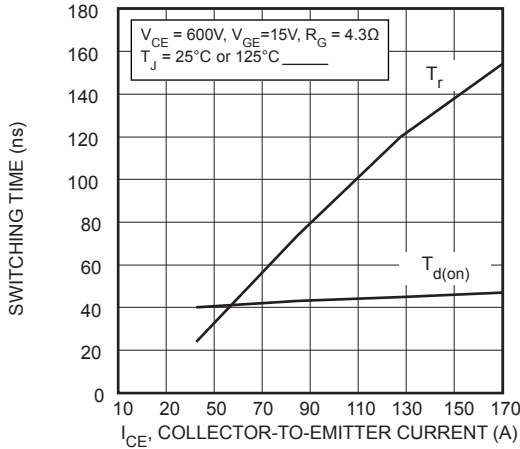


FIGURE 12, Turn-On Time vs Collector Current

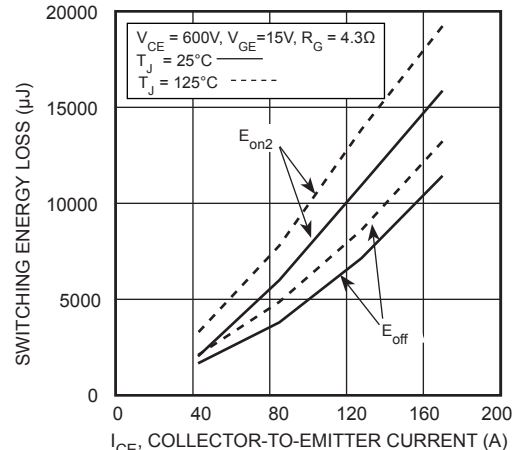


FIGURE 14, Energy Loss vs Collector Current

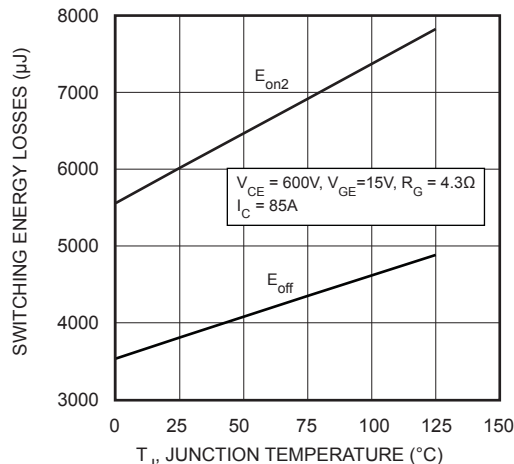


FIGURE 16, Switching Energy vs Junction Temperature

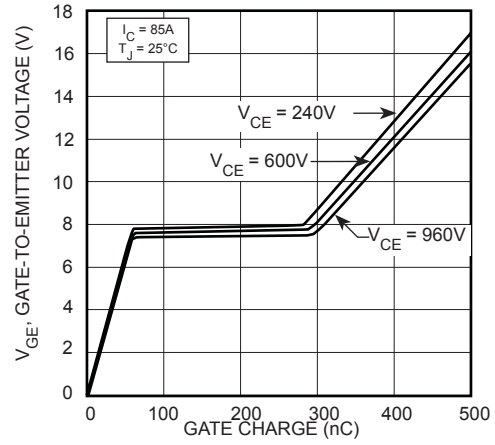


FIGURE 11, Gate charge

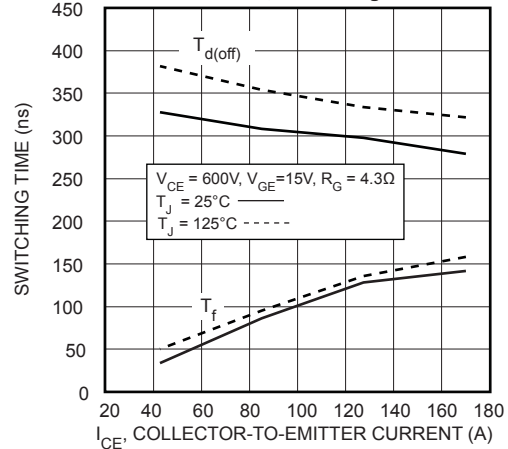


FIGURE 13, Turn-Off Time vs Collector Current

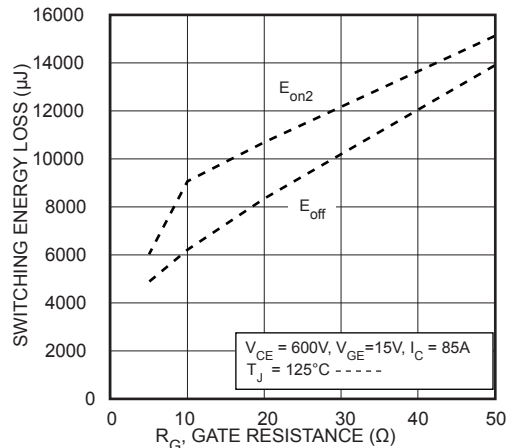


FIGURE 15, Energy Loss vs Gate Resistance

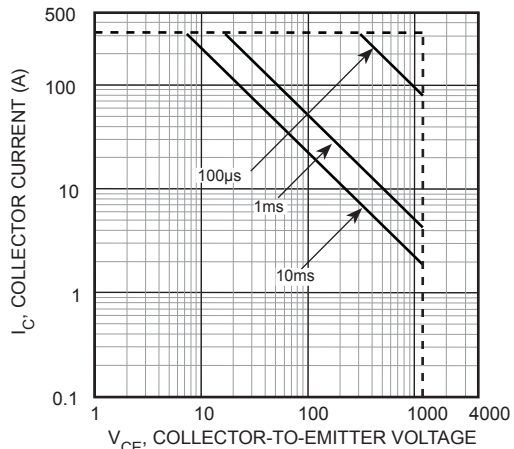
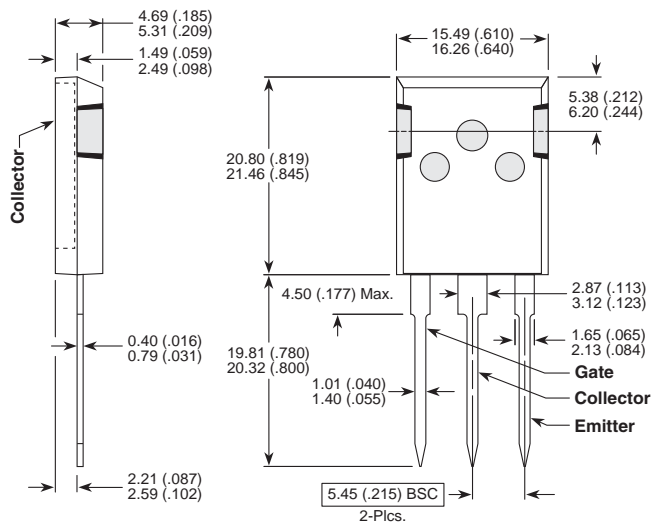


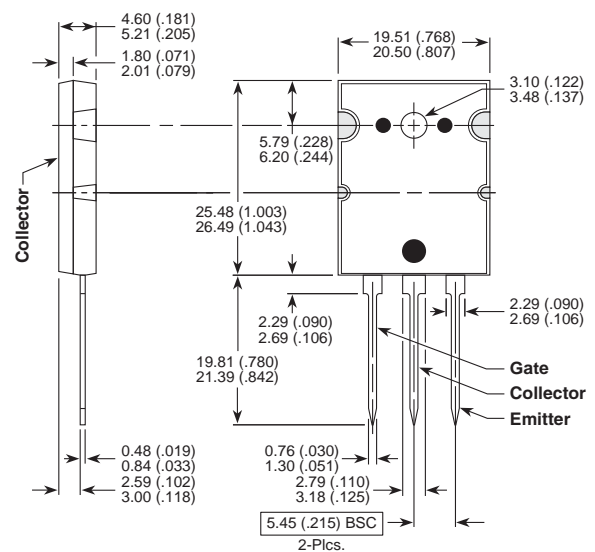
FIGURE 17, Minimum Switching Safe Operating Area

**T-MAX™ (B2) Package Outline**



These dimensions are equal to the TO-247 without the mounting hole.  
 Dimensions in Millimeters and (Inches)

**TO-264 (L) Package Outline**



Dimensions in Millimeters and (Inches)

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